

Vladimir N Poroshin

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Resistive switching effect in the n -InGaAs/GaAs heterostructures with double tunnel-coupled quantum wells. <i>Low Temperature Physics</i> , 2022, 48, 157-160.	0.6	1
2	Electric transport properties in the 2D-MoS ₂ . <i>Molecular Crystals and Liquid Crystals</i> , 2022, 749, 87-92.	0.9	2
3	Transient processes in electric transport in the powder MoS ₂ samples. <i>Journal of Applied Physics</i> , 2022, 131, .	2.5	1
4	Specific interactions and charge transport in ternary PVDF/polyaniline/MWCNT nanocomposite films. <i>Composites Science and Technology</i> , 2020, 198, 108284.	7.8	11
5	Effect of barrier width between GaAs/InGaAs/GaAs double coupled quantum wells on bipolar transport and terahertz radiation by hot carriers in lateral electric field. <i>Low Temperature Physics</i> , 2020, 46, 633-638.	0.6	3
6	Multifunctionality of lanthanum-strontium manganite nanopowder. <i>Physical Chemistry Chemical Physics</i> , 2020, 22, 11817-11828.	2.8	28
7	The effect of structure on the low-temperature electrical conductivity of carbon nanocomposite temperature sensors. <i>Low Temperature Physics</i> , 2019, 45, 1104-1108.	0.6	1
8	Magnetoresistance of composite carbon sensors in strong electric fields in the liquid helium temperature range. <i>Low Temperature Physics</i> , 2017, 43, 367-370.	0.6	2
9	Transformation of graphene flakes into carbon nanostructures by γ -irradiation. <i>Materials Research Express</i> , 2017, 4, 045602.	1.6	1
10	A peculiarity of quantum hot-electron real space transfer in dual-channel GaAs-based heterostructures. <i>Journal of Physics Communications</i> , 2017, 1, 045002.	1.2	3
11	Interaction of surface plasmon polaritons in heavily doped GaN microstructures with terahertz radiation. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	22
12	Interband and intraband radiation from the n -InGaAs/GaAs heterostructures with quantum wells under the conditions of injection in high lateral electric fields. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2015, 74, 328-333.	2.7	4
13	On some new effects in delta-doped QWs. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2015, 66, 162-169.	2.7	10
14	Terahertz emission and reflection associated with surface plasmon polaritons in n -GaN microstructures. , 2014, , .		0
15	Influence of conduction via a channel of an impurity δ -layer on the magneto-quantum effects in AlGaAs/GaAs/AlGaAs heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2014, 60, 31-36.	2.7	5
16	Far-infrared radiation from n -InGaAs/GaAs quantum-well heterostructures in high lateral electric fields under injection conditions. <i>Semiconductors</i> , 2014, 48, 625-629.	0.5	2
17	Long-term photoconductivity decay in n -InGaAs/GaAs heterostructures with coupled quantum wells under band-to-band excitation. <i>Semiconductors</i> , 2013, 47, 174-177.	0.5	3
18	Tin induced a -Si crystallization in thin films of Si-Sn alloys. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	26

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19	On the possibility of tuning the energy separation between space-quantized levels in a quantum well. Philosophical Magazine Letters, 2013, 93, 42-49.	1.2	10
20	Negative residual infrared photoconduction in the p-SiGe/Si heterostructures with selectively doped quantum wells. Journal of Applied Physics, 2012, 112, 083715.	2.5	0
21	Transport properties of InGaAs/GaAs Heterostructures with δ -doped quantum wells. Semiconductors, 2012, 46, 631-636.	0.5	9
22	Does the Temperature Dependence of the Charge Carrier Mobility in Disordered Organic Semiconductors at Large Carrier Concentrations Obey the Meyer-Neldel Compensation Law?. Molecular Crystals and Liquid Crystals, 2011, 535, 1-9.	0.9	5
23	Lateral transport and far-infrared radiation of electrons in $\text{In}_{1-x}\text{Ga}_x\text{As}/\text{GaAs}$ heterostructures with the double tunnel-coupled quantum wells in a high electric field. Semiconductors, 2010, 44, 1495-1498.	0.5	9
24	Dependence of Meyer-Neldel energy on energetic disorder in organic field effect transistors. Applied Physics Letters, 2010, 96, 213306.	3.3	41
25	Nature of damped current oscillations in the formation of a static acoustoelectric domain in a n-InGaAs/GaAs quantum-well heterostructure. Semiconductors, 2008, 42, 589-592.	0.5	4
26	Energy characteristics of boron impurity in $\text{Si}_{1-x}\text{Ge}_x$ heterostructures with on-center and on-edge selective doping of quantum wells. Low Temperature Physics, 2007, 33, 869-871.	0.6	1
27	<title>Resonant intersubband transitions of holes in uniaxially stressed p-Ge</title>. , 2001, , .		0
28	<title>Screened Coulomb potential approach for the study of resonant impurity states in uniaxially deformed p-Ge</title>. , 2001, , .		1
29	Infrared light scattering by free holes in p-Ge. Semiconductor Science and Technology, 1994, 9, 1790-1794.	2.0	1
30	Self-induced birefringence of infrared light in Ge. Physical Review Letters, 1993, 71, 3027-3030.	7.8	2
31	Electron and photon emission from discontinuous carbon films. International Journal of Electronics, 1992, 73, 1005-1008.	1.4	3
32	Limit of transient heat absorption by superfluid helium for very large heat pulses. Cryogenics, 1989, 29, 444-447.	1.7	9
33	Investigation of Nonequilibrium Phonons in GaAs. Physica Status Solidi (B): Basic Research, 1986, 136, 63-68.	1.5	4
34	Measurement of the transient heat transfer to liquid helium from a thin metal film. Cryogenics, 1983, 23, 546-548.	1.7	11